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47395549 Fundamental Of Microelectronics Bahzad Razavi Chapter 2 Solution Manual. = $4.124 \times 10^{16} \text{ cm}^{-3}$ Compared to the values obtained in Example 2.1, we can see that the intrinsic carrier concentration n_i in Ge at $T = 300 \text{ K}$ is $2.465 \times 10^{13} \text{ cm}^{-3}$ $1.08 \times 10^{10} = 2282$ times higher than the intrinsic carrier concentration in Si at $T = 300 \text{ K}$. Similarly, at $T = 600 \text{ K}$, the intrinsic carrier concentration in Ge is 26.8 times higher than that in Si.

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